

SWITCHMODE™ Power Rectifiers

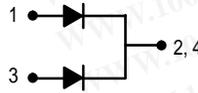
... using the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

- Guardring for Stress Protection
- Low Forward Voltage
- 150°C Operating Junction Temperature
- Guaranteed Reverse Avalanche
- Epoxy Meets UL94, VO at 1/8"

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 1.9 grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Shipped 50 units per plastic tube
- Marking: B2035, B2045

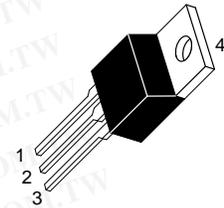
勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-34970699
 勝特力电子(深圳) 86-755-83298787
 Http://www.100y.com.tw



MBR2035CT
MBR2045CT

MBR2045CT is a
Motorola Preferred Device

**SCHOTTKY BARRIER
RECTIFIERS**
20 AMPERES
35 and 45 VOLTS



CASE 221A-06
TO-220AB
PLASTIC

MAXIMUM RATINGS

Rating	Symbol	MBR2035CT	MBR2045CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	35	45	Volts
Average Rectified Forward Current (Rated V_R) $T_C = 135^\circ\text{C}$	$I_{F(AV)}$	20	20	Amps
Peak Repetitive Forward Current Per Diode Leg (Rated V_R , Square Wave, 20 kHz) $T_C = 135^\circ\text{C}$	I_{FRM}	20	20	Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	150	150	Amps
Peak Repetitive Reverse Surge Current (2.0 μs , 1.0 kHz) See Figure 11	I_{RRM}	1.0	1.0	Amp
Operating Junction Temperature	T_J	-65 to +150	-65 to +150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +175	-65 to +175	$^\circ\text{C}$
Voltage Rate of Change (Rated V_R)	dv/dt	1000	1000	$\text{V}/\mu\text{s}$

THERMAL CHARACTERISTICS

Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.0	2.0	$^\circ\text{C}/\text{W}$
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ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage (1) ($i_F = 10$ Amps, $T_C = 125^\circ\text{C}$) ($i_F = 20$ Amps, $T_C = 125^\circ\text{C}$) ($i_F = 20$ Amps, $T_C = 25^\circ\text{C}$)	v_F	0.57 0.72 0.84	0.57 0.72 0.84	Volts
Maximum Instantaneous Reverse Current (1) (Rated dc Voltage, $T_C = 125^\circ\text{C}$) (Rated dc Voltage, $T_C = 25^\circ\text{C}$)	i_R	15 0.1	15 0.1	mA

(1) Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

SWITCHMODE is a trademark of Motorola, Inc.

Preferred devices are Motorola recommended choices for future use and best overall value.

MBR2035CT MBR2045CT

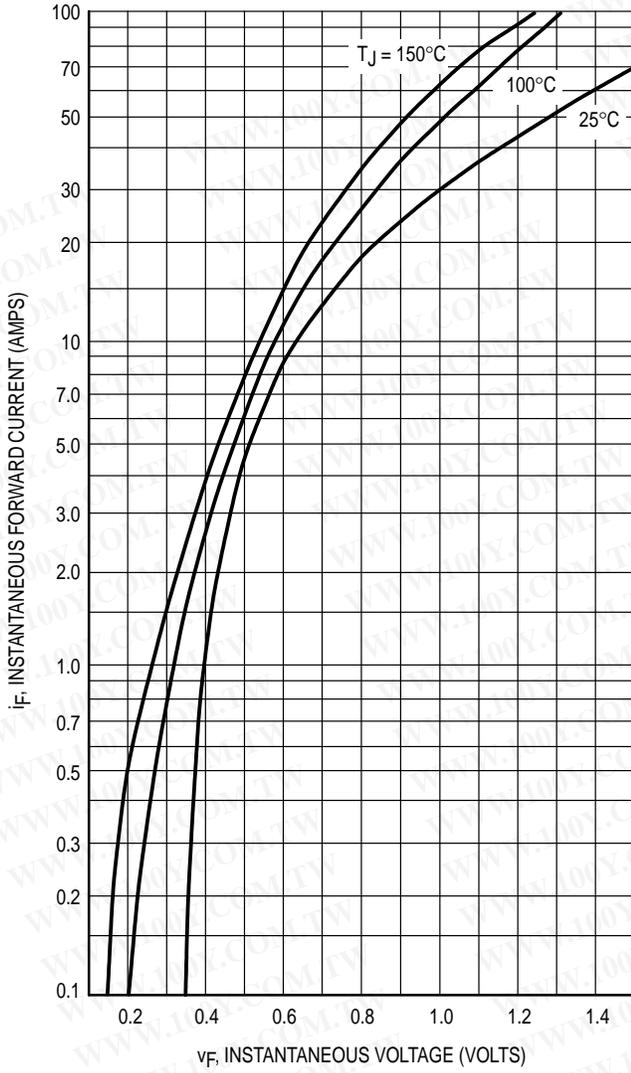


Figure 1. Maximum Forward Voltage

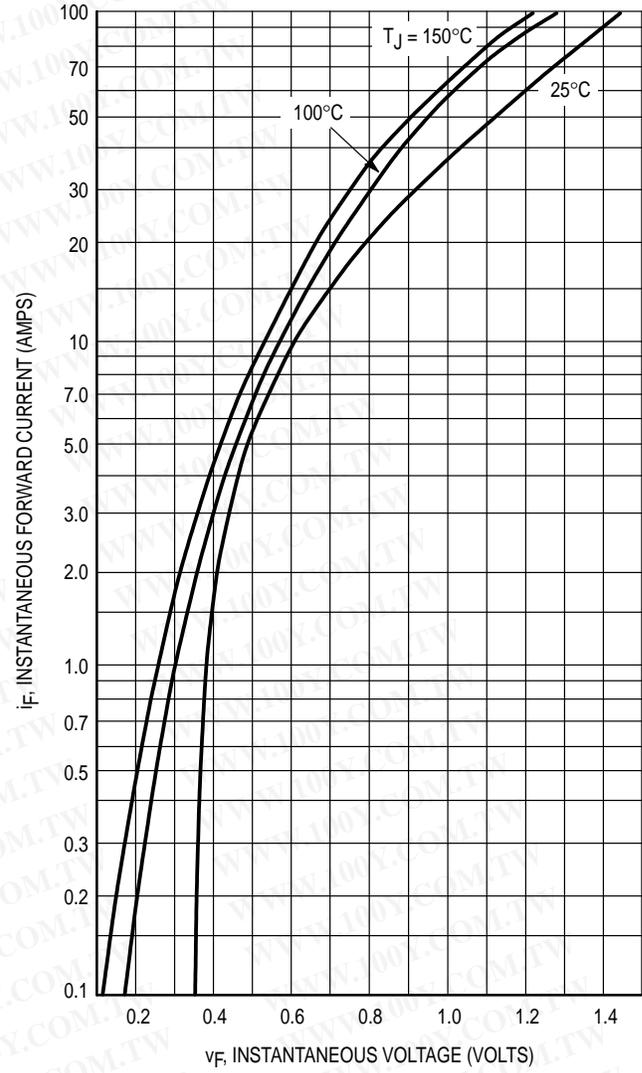


Figure 2. Typical Forward Voltage

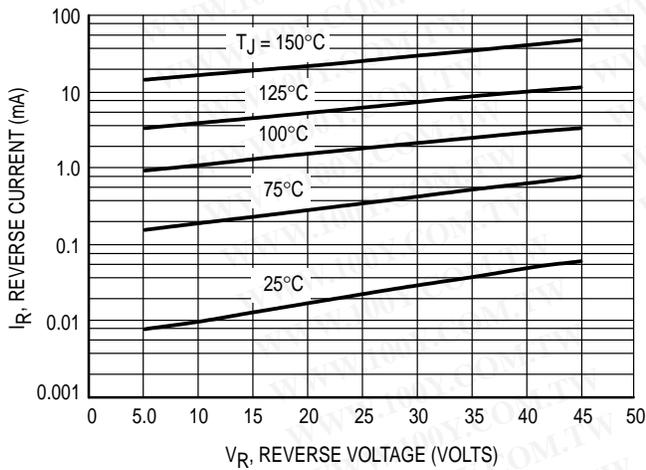


Figure 3. Maximum Reverse Current

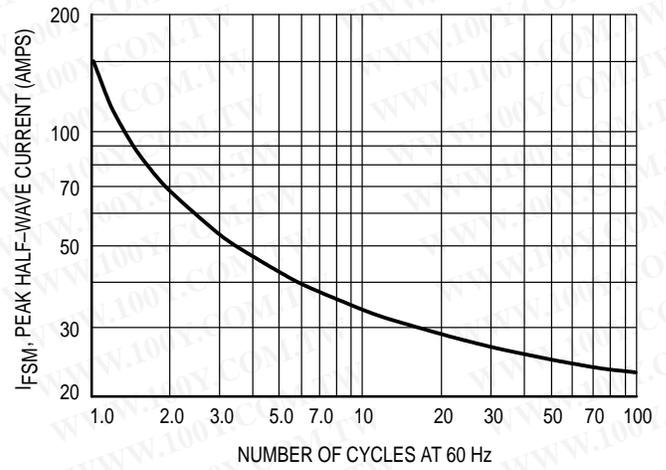


Figure 4. Maximum Surge Capability

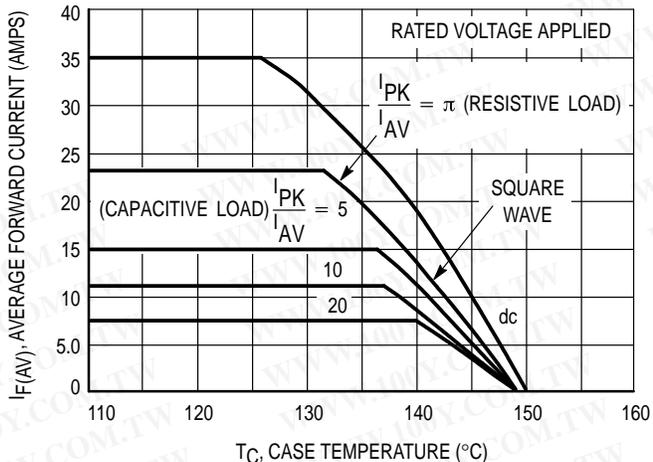


Figure 5. Current Derating, Infinite Heatsink

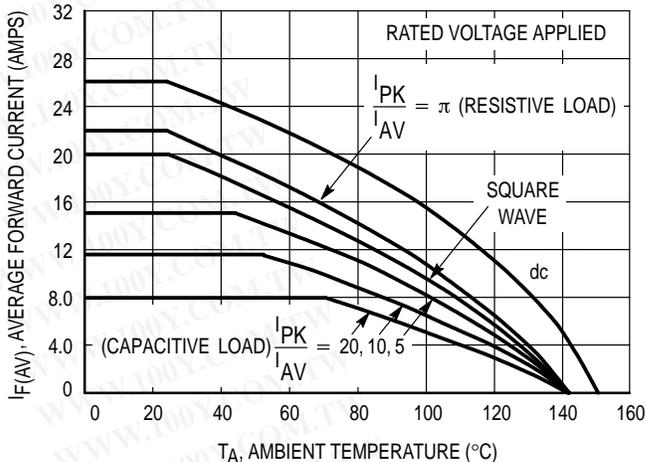


Figure 6. Current Derating, $R_{\theta JA} = 16^{\circ}\text{C/W}$

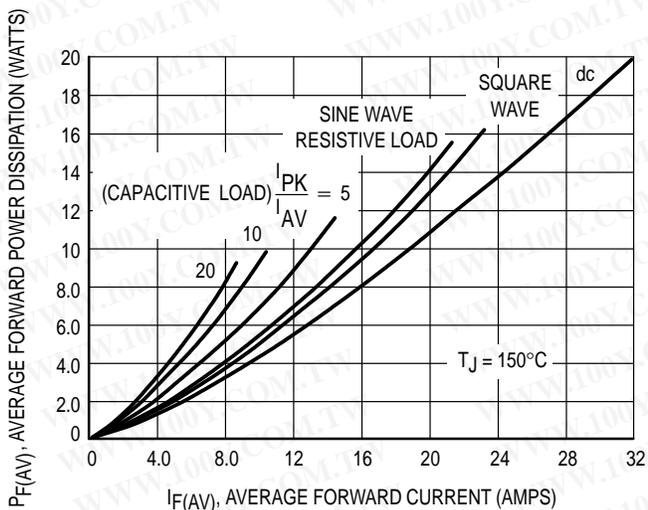


Figure 7. Forward Power Dissipation

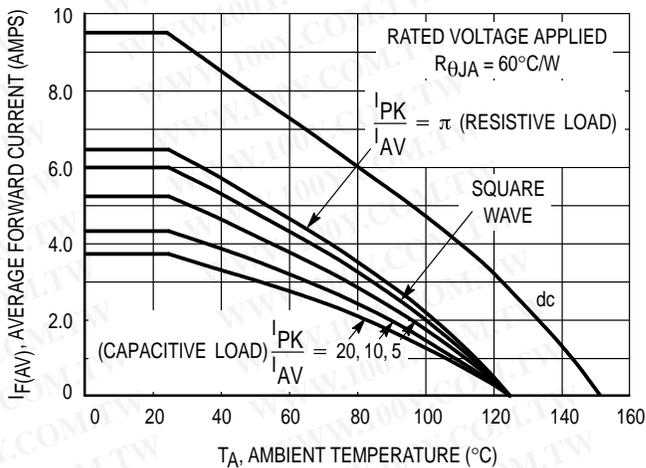


Figure 8. Current Derating, Free Air

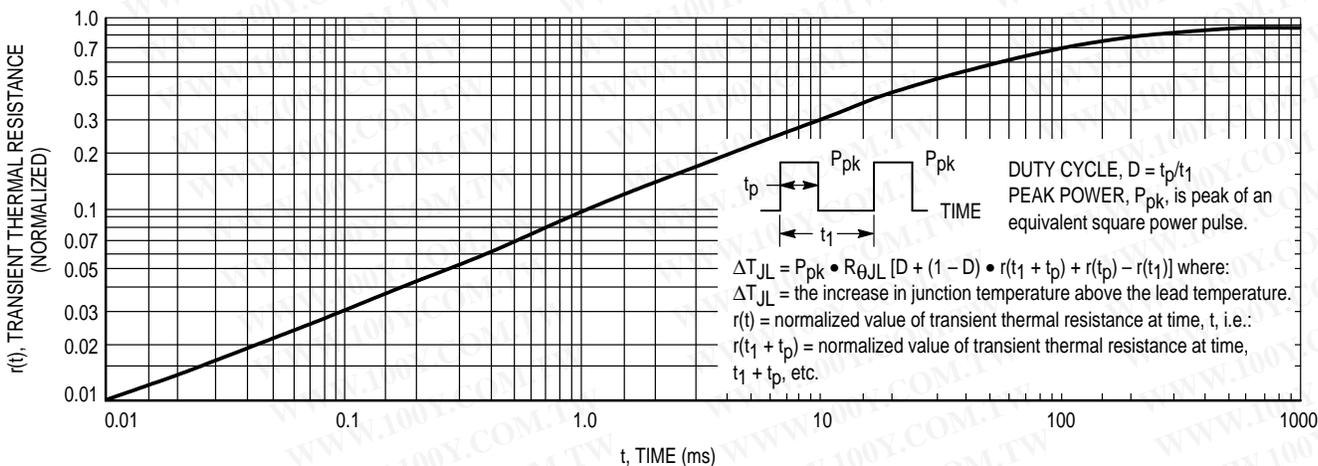


Figure 9. Thermal Response

HIGH FREQUENCY OPERATION

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 10.)

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 percent at 2.0 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficiency is not indicative of power loss; it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.

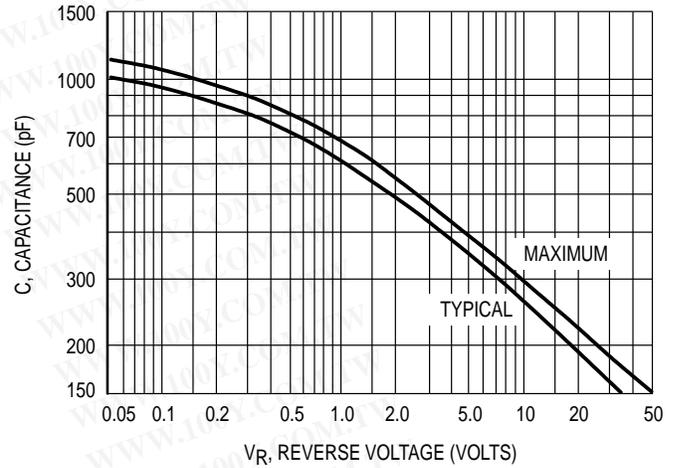


Figure 10. Capacitance

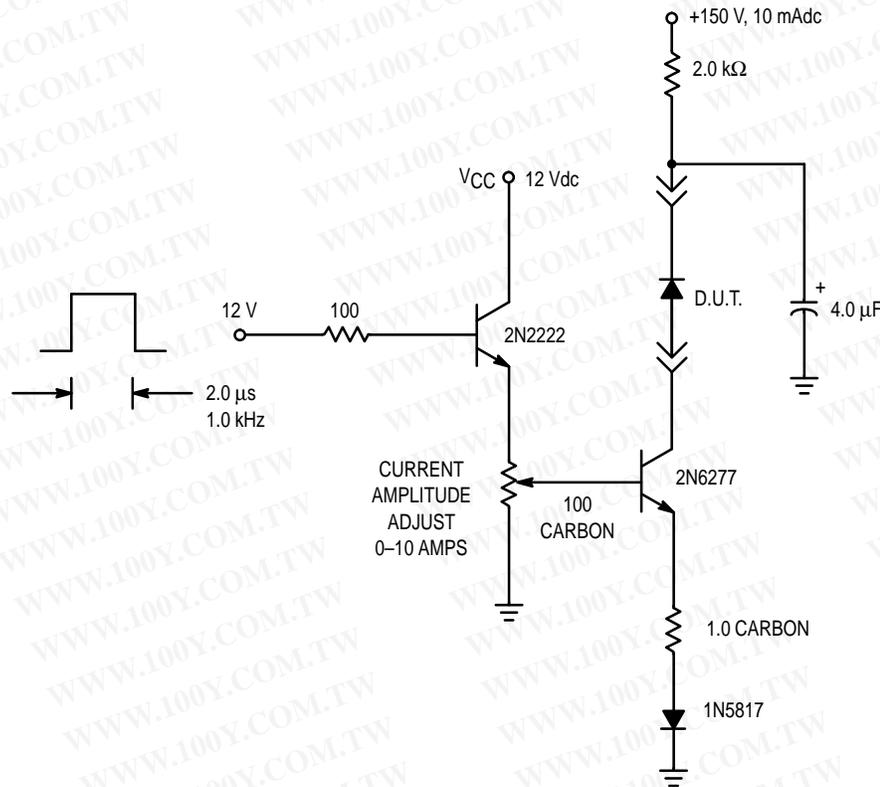
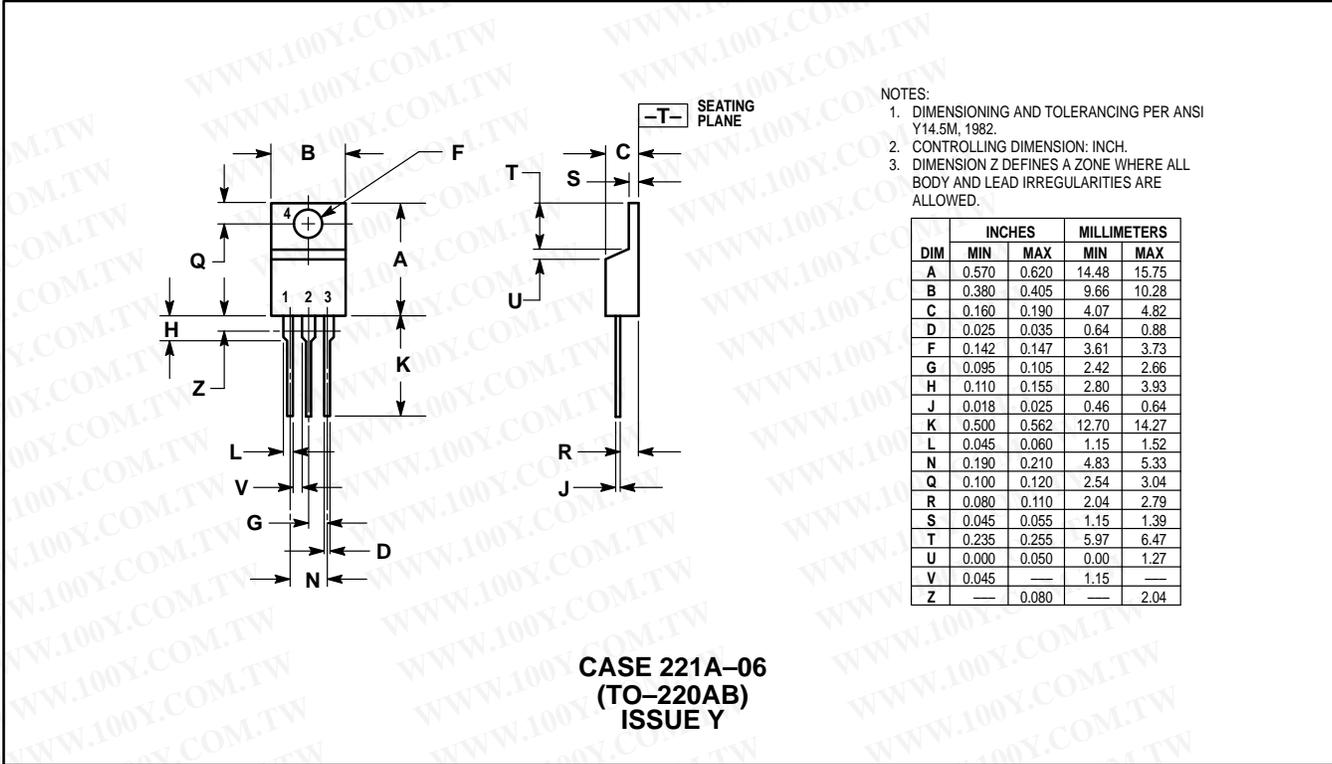


Figure 11. Test Circuit for dv/dt and Reverse Surge Current

PACKAGE DIMENSIONS



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